THE DEFECTIVE SUBSYSTEM OF THIN PbSe FILMS UNDER VAPOUR-PHASE EPITAXY WITH PARTICIPATION OF OXYGEN

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S u m m a r y

The complex spectrum of charge states of intrinsic atomic Frenkel defects in the lead selenide cationic sublattice and of impurity acceptor centers with participation of oxygen is proposed. The influence of technology factors in the hot-wall method on the redistribution of defects in *n*- and *p*-types of PbSe films is established.